

S/N 10/028643



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner:	Long Pham
Serial No.:	10/028,643	Group Art Unit:	2814
Filed:	December 20, 2001	Docket:	1303.030US1
Title:	LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO ₃ GATE DIELECTRICS		

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

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Serial No :10/028643

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The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

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David C. Peterson

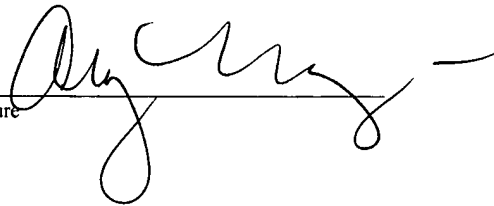
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Application Number 10/028,643

Filing Date December 20, 2001

First Named Inventor Ahn, Kie

Group Art Unit 2814

Examiner Name Pham, Long

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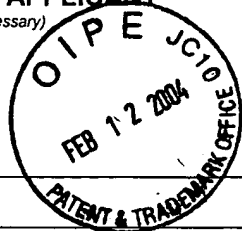
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Group Art Unit	2814
Examiner Name	Pham, Long

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Attorney Docket No: 1303.030US1

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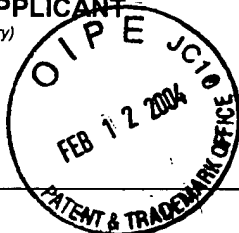
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